

Features

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications

- AC controllers
- DC and AC motor control
- Controlled rectifiers

$I_{T(AV)}$ **420A**
 V_{DRM}/V_{RRM} **5600~6500V**
 I_{TSM} **4.5 kA**
 I^2t **101 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Double side cooled	T _C =70°C	125		420	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms	125	5600		6500	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			150	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			4.5	kA
I ² t	I ² t for fusing coordination	V _R =0.6V _{RRM}				101	A ² s*10 ³
V _{TO}	Threshold voltage		125			1.25	V
r _T	On-state slope resistance					2.20	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =1000A, F=15kN	125			3.50	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			2000	V/μs
di/dt	Critical rate of rise of on-state current	V _{DM} = 67%V _{DRM} to1300A, Gate pulse t _r ≤0.5μs I _{GM} =1.5A	125			100	A/μs
Q _{rr}	Recovery charge	I _{TM} =2000A, tp=2000μs, di/dt=-5A/μs, V _R =50V	125		2000		μC
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	40		300	mA
V _{GT}	Gate trigger voltage			0.8		3.0	V
I _H	Holding current			25		200	mA
V _{GD}	Non-trigger gate voltage	V _{DM} =0.67V _{DRM}	125	0.3			V
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force15kN				0.035	°C/W
R _{th(c-h)}	Thermal resistance case to heatsink					0.008	°C/W
F _m	Mounting force			10	15	20	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				240		g
Outline							

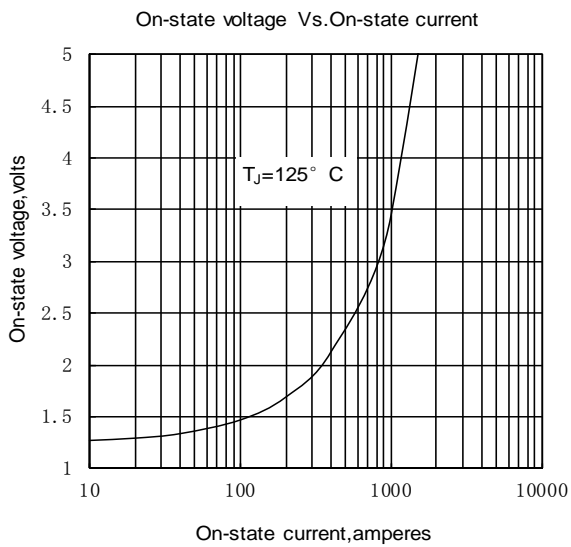


Fig. 1

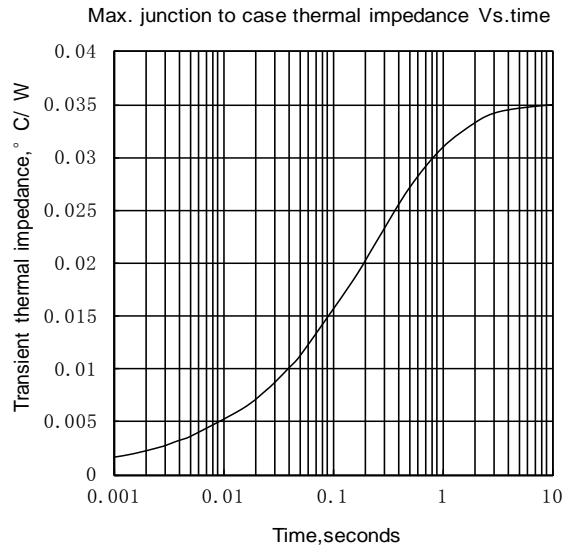


Fig. 2

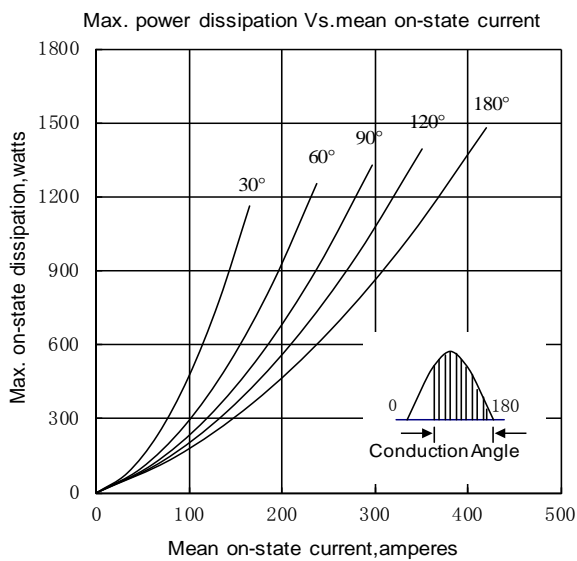


Fig. 3

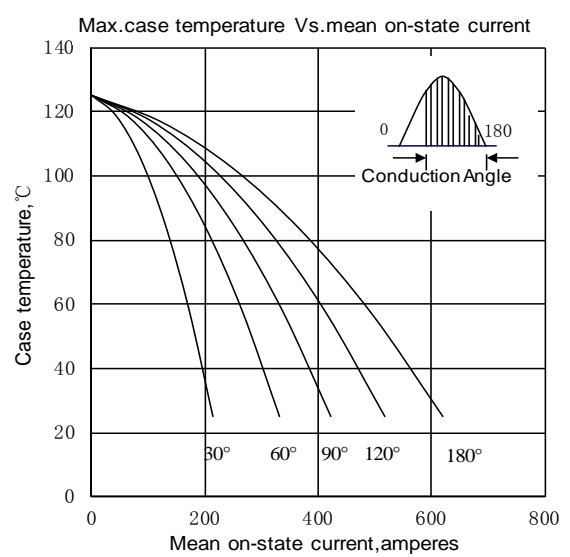


Fig. 4

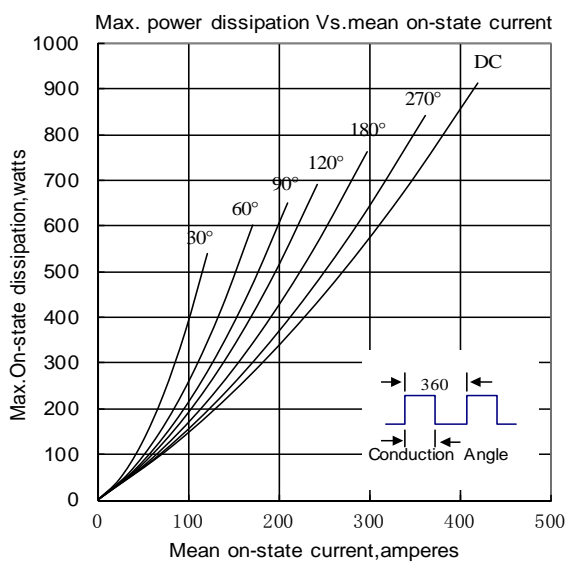


Fig. 5

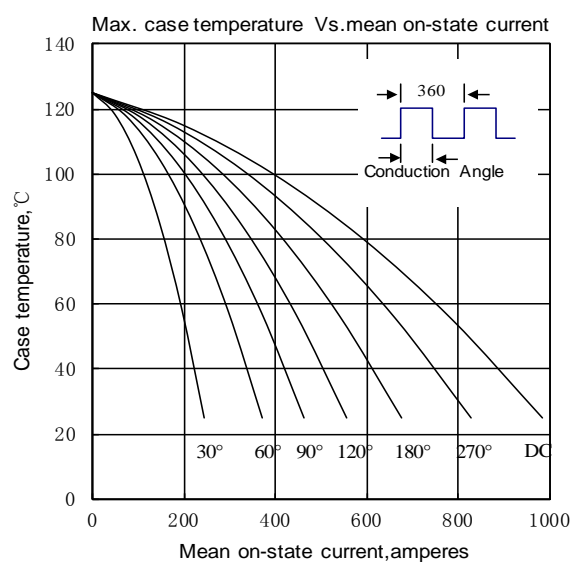


Fig. 6

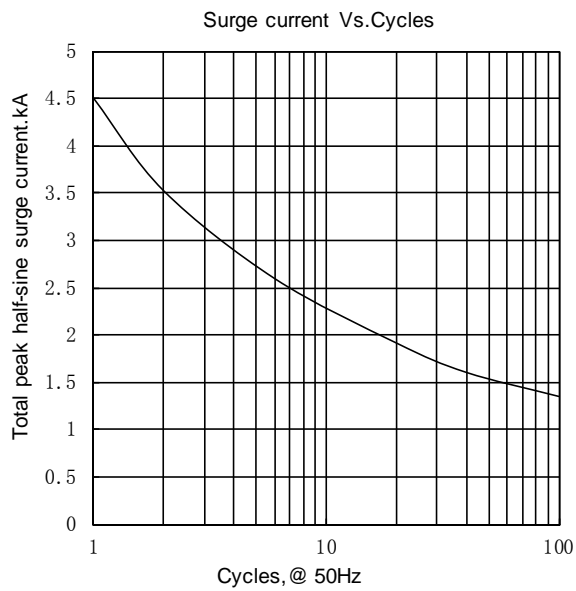


Fig.7

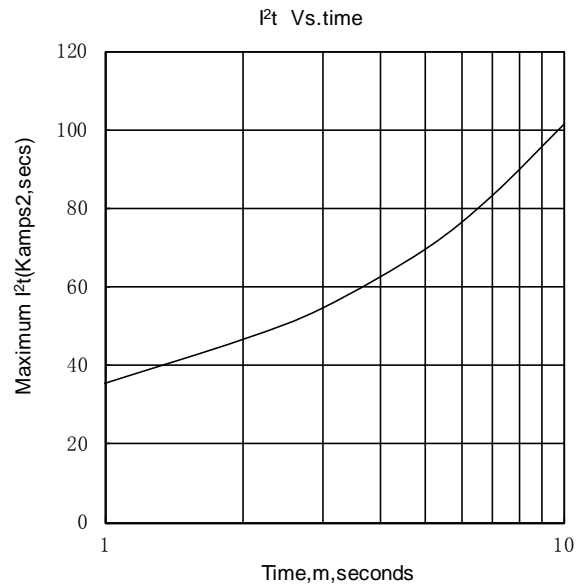


Fig.8

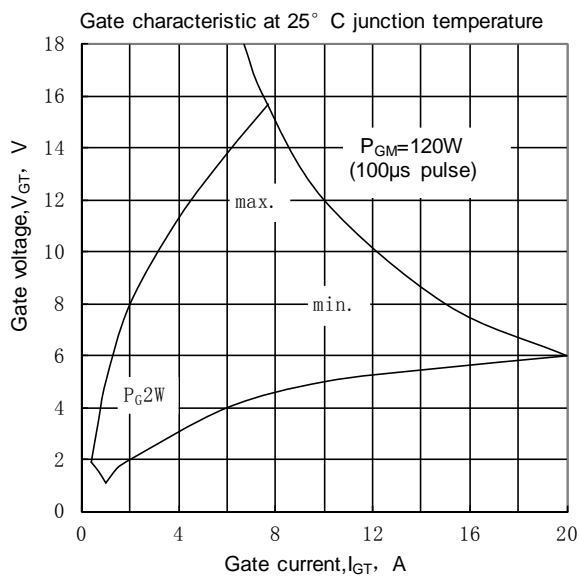


Fig.9

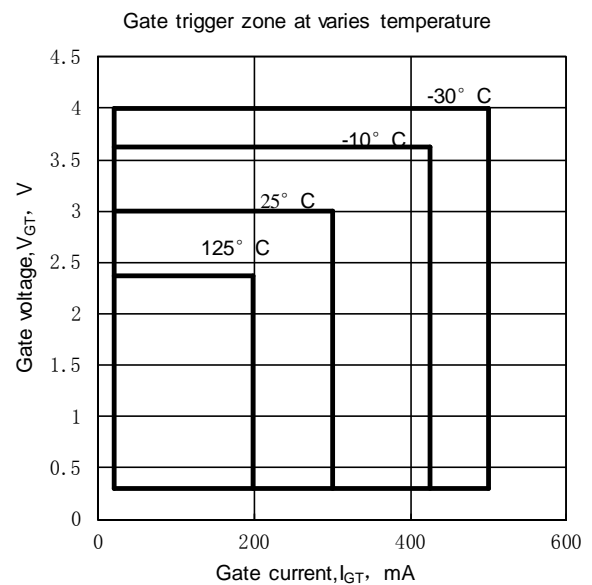


Fig.10

Outline:

